

ABSTRACT

A new method to form a SRAM memory cell in an integrated circuit device is achieved. The method comprises providing a bi-stable flip-flop cell having a data storage node and a data bar storage node. A first capacitor is formed coupled to the data bar storage node, and a second capacitor is formed coupled to the data storage node. The first and second capacitors comprise a first conductor layer overlying a second conductor layer with a dielectric layer therebetween. One of the first and second conductor layers is coupled to ground. A new SRAM device is disclosed.